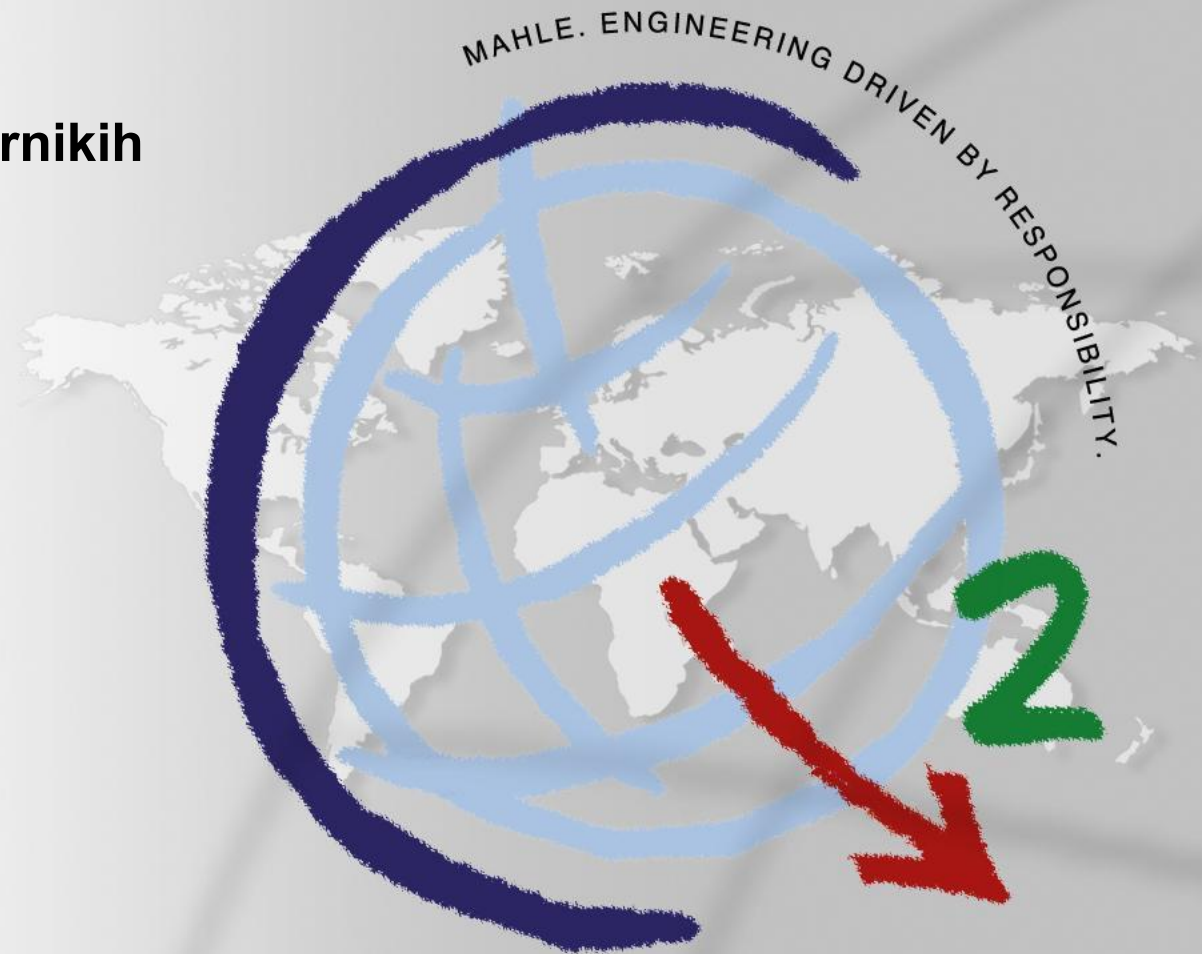


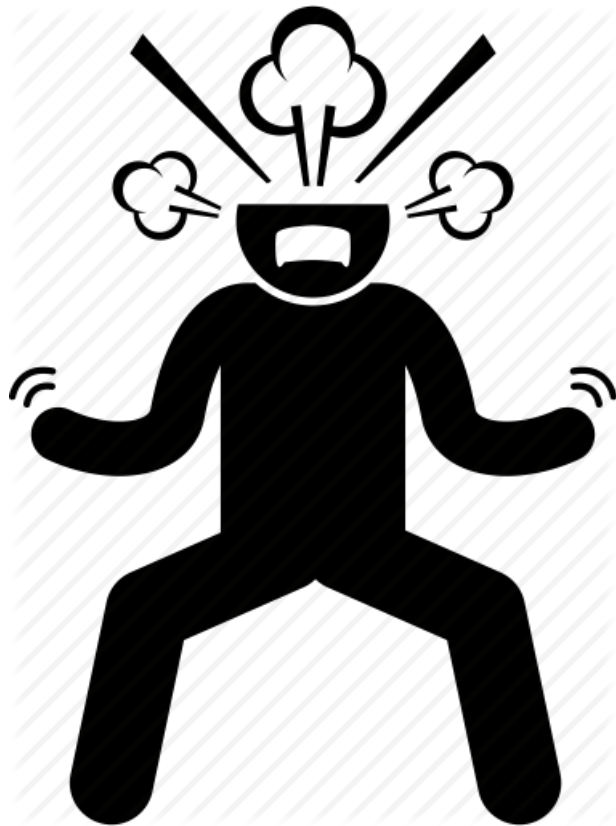
Preklopi pri močnostnih pretvornikih

Jernej Sorta
Električni pogoni
ELP

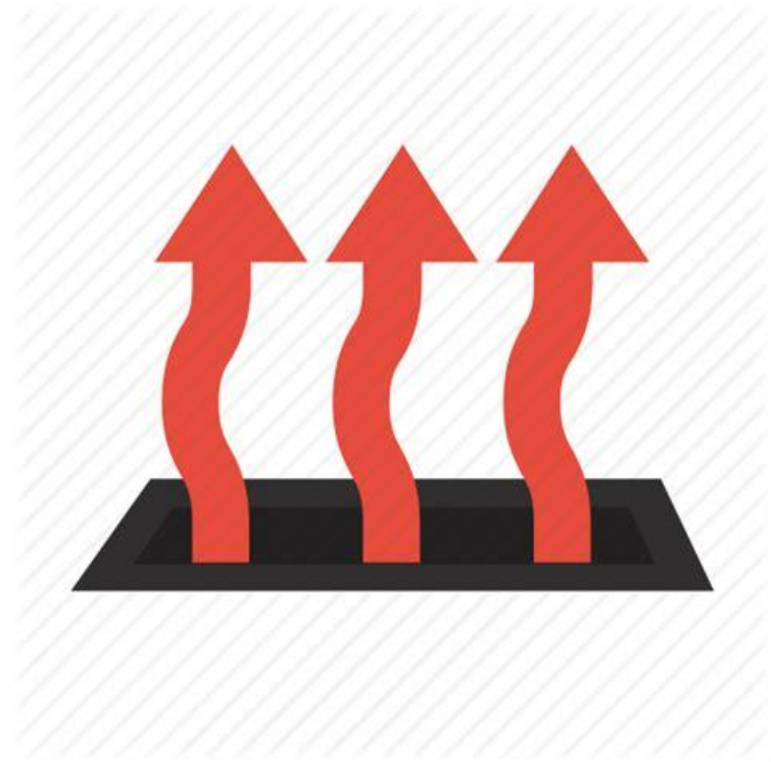


Zakaj je dobro poznati
pojave ob preklopu?

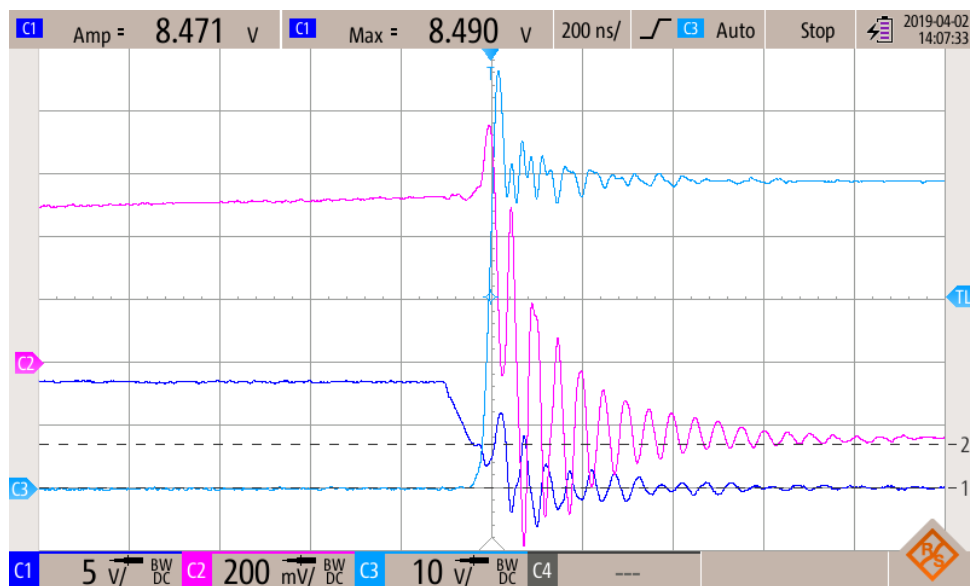
■ EMC



■ Izkoristek



■ Prej

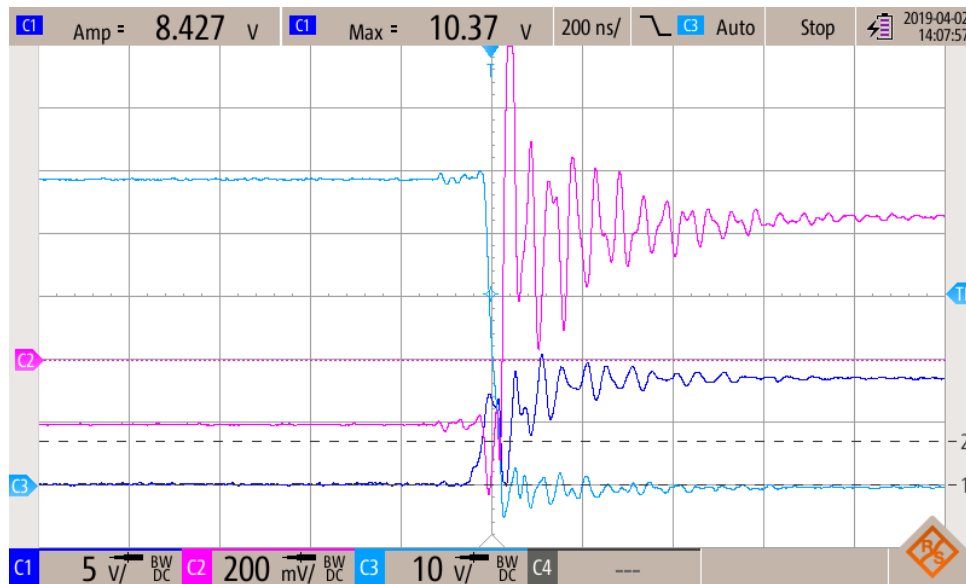


■ Potem



U_{gs}, I_s, U_{ds}

■ Prej



■ Potem



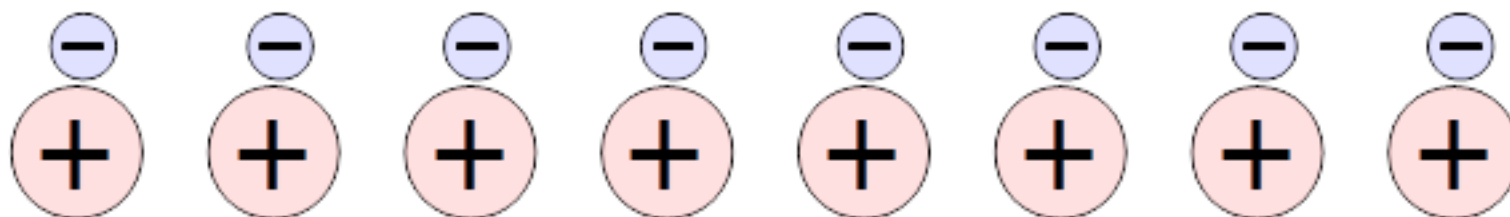
U_{gs}, I_s, U_{ds}

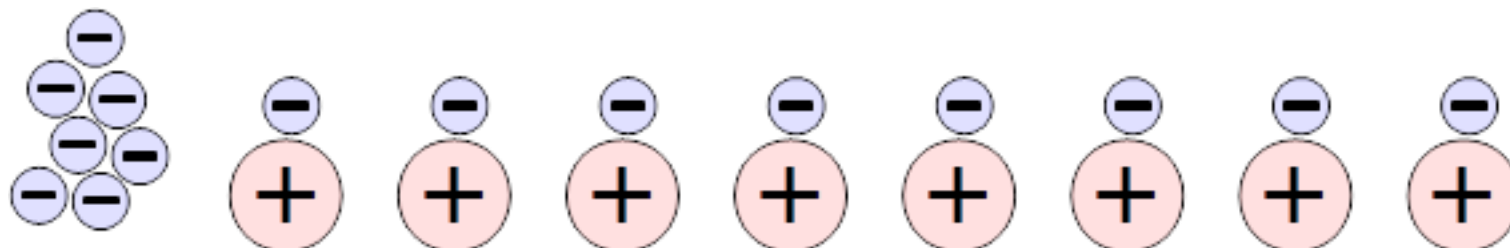
Zakaj preklopi?

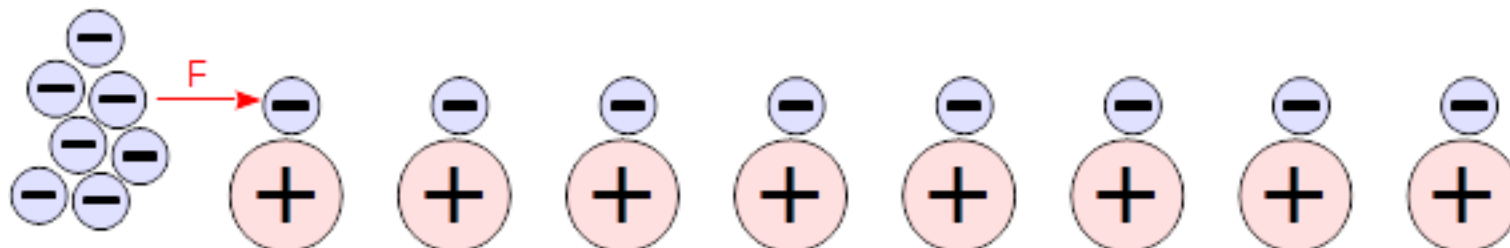
MAHLE

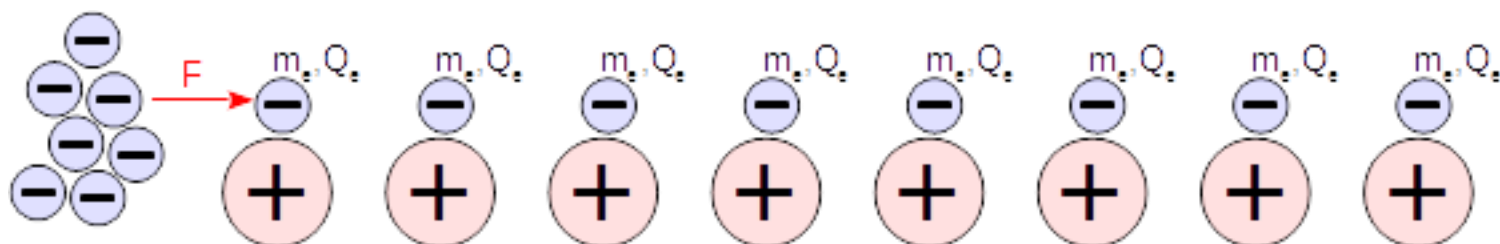
Driven by performance

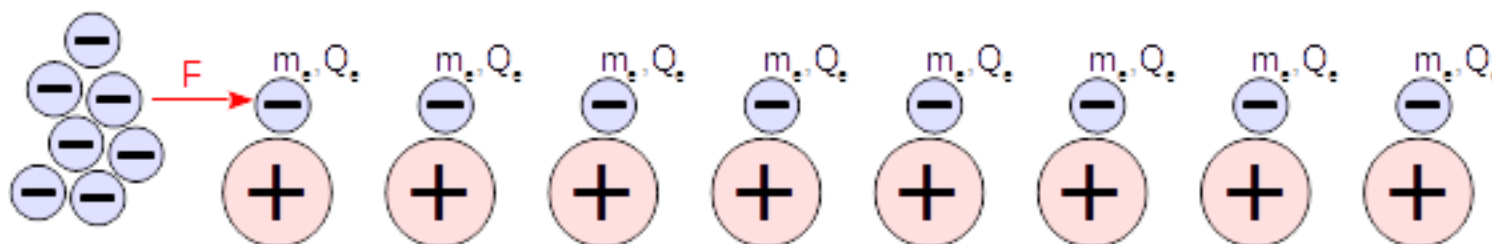


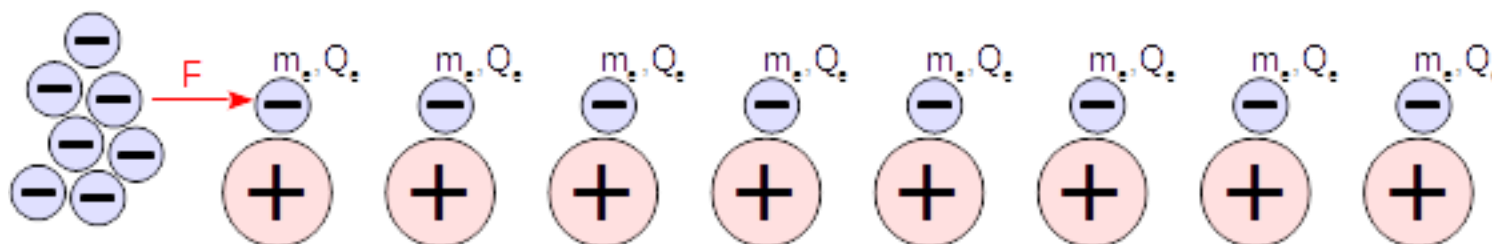






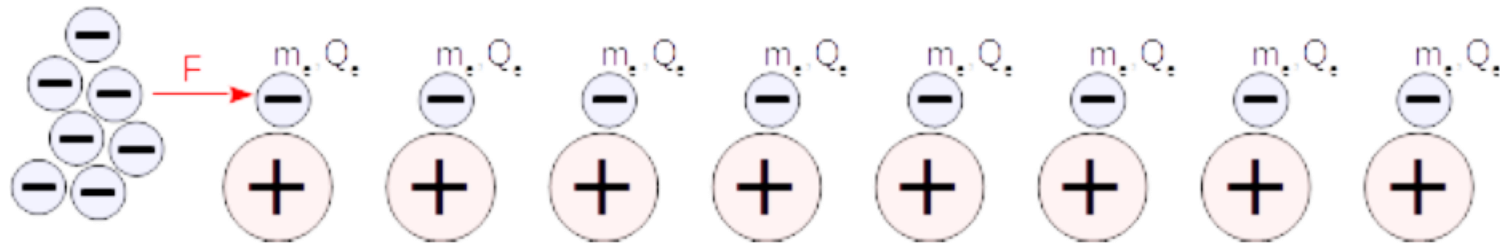






$$\frac{d}{dt}(m_e v_e) = F$$

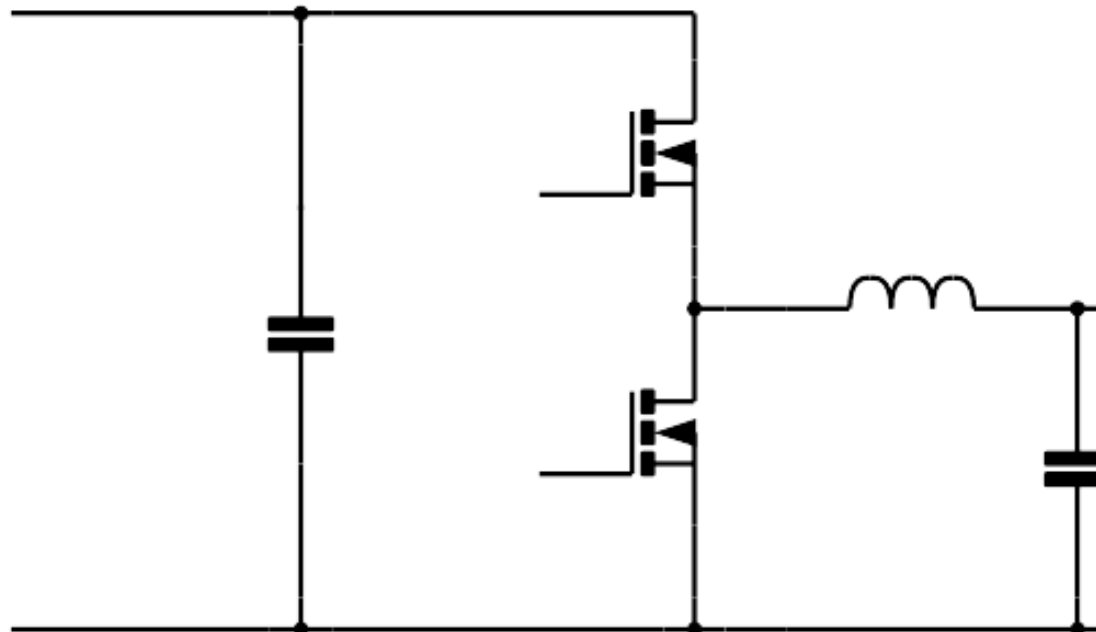
$$v_e \cdot Q_e \propto I$$

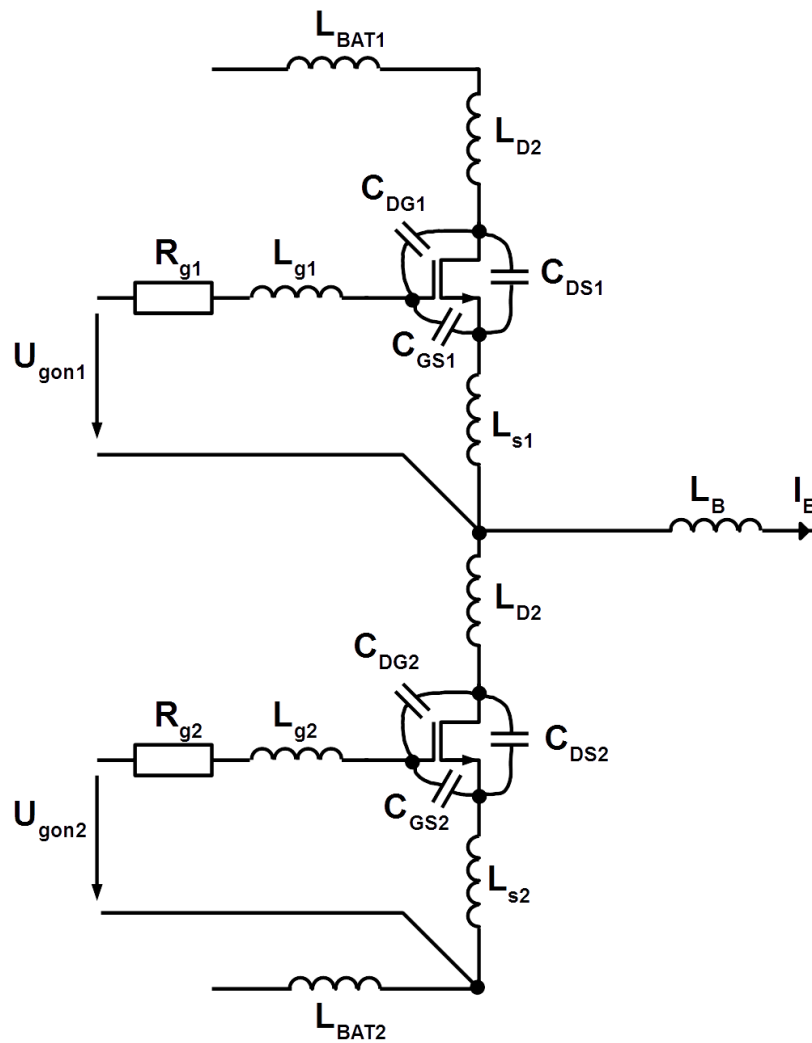


$$\frac{d}{dt}(m_e v_e) = F$$

$$v_e \cdot Q_e \propto I$$

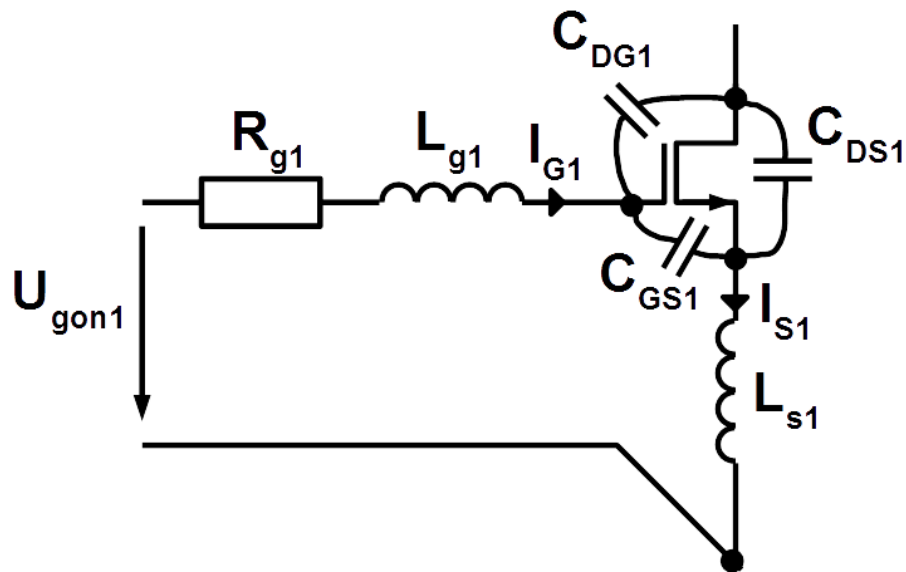
$$m \frac{dI}{dt} \propto F \longleftrightarrow L \frac{dI}{dt} = U_L$$





- Tok teče v breme
- Spodnji tranzistor je izklopljen, tok teče skozi notranjo diodo
- Gornji tranzistor je izklopljen
- Priključimo Ugon1 (stopnica)

Preklop toka

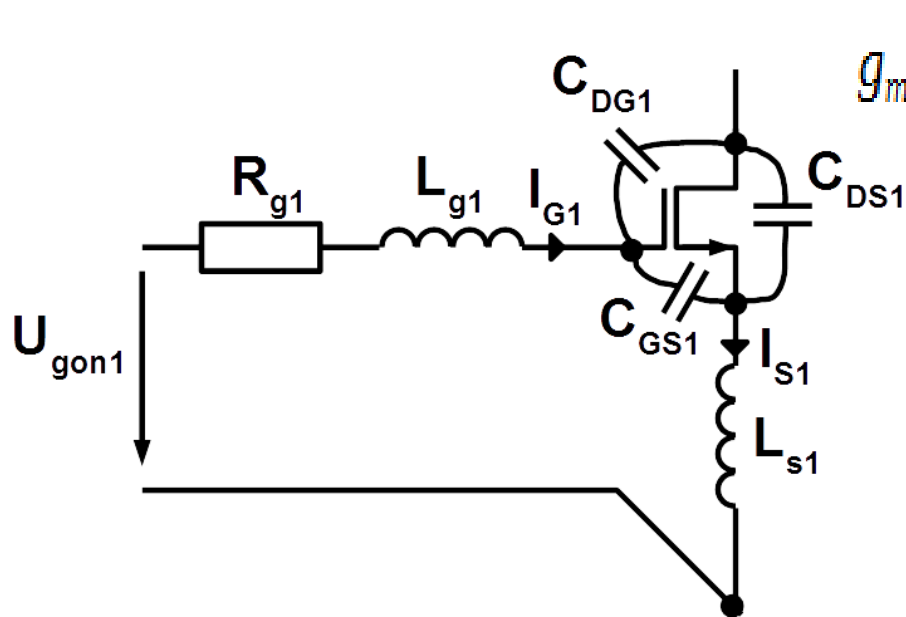


$$U_{gon1} = R_g \cdot I_g + L_g \cdot I_g' + U_{GS} + L_s \cdot I_s'$$

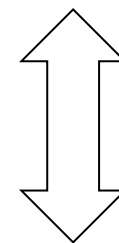
$$I_g \approx C_{GS} \cdot U_{GS}'$$

$$I_{DS} \approx U_{GS} \cdot g_m$$

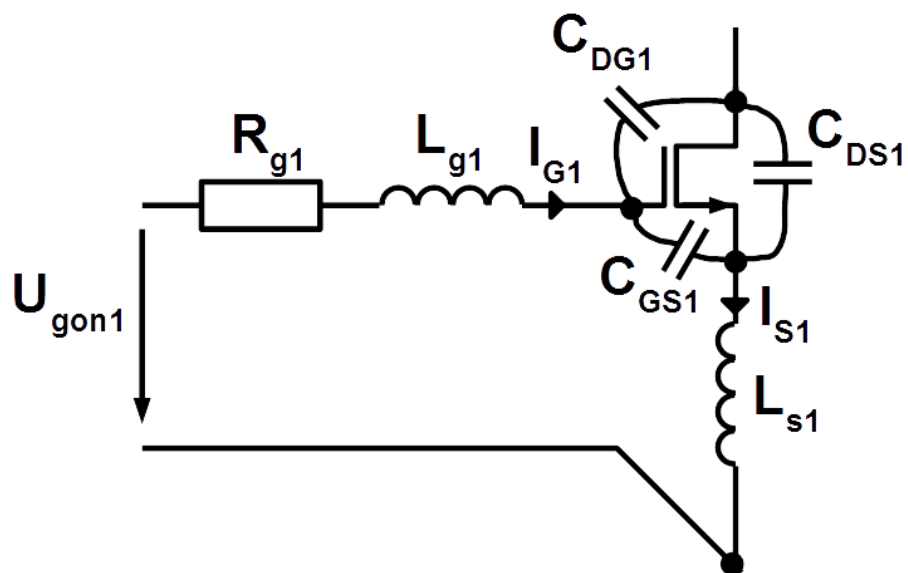
$$I_S = I_g + I_{DS}$$



$$g_m \cdot U_{gon1} = I_{DS}'' (L_s + L_g) C_{GS} + I_{DS}' (g_m L_s + R_g C_{GS}) + I_{DS}$$

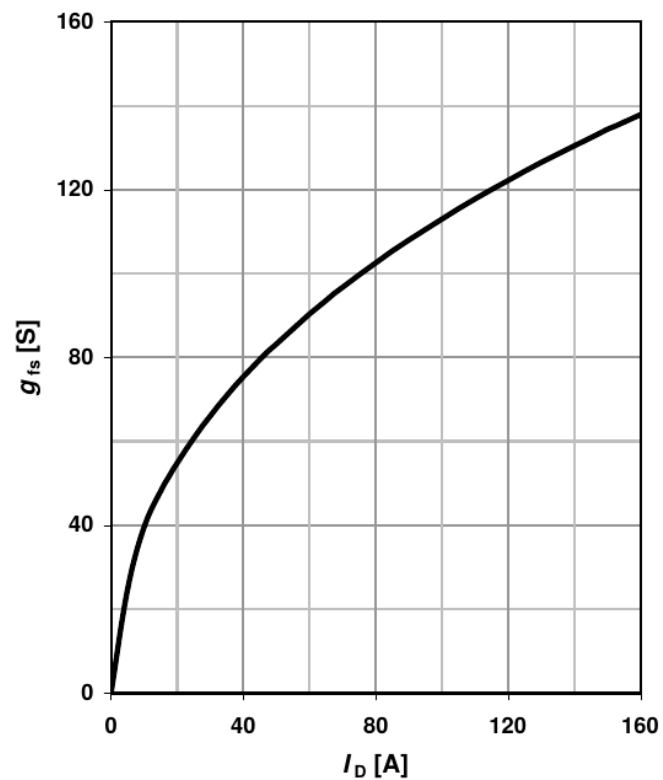
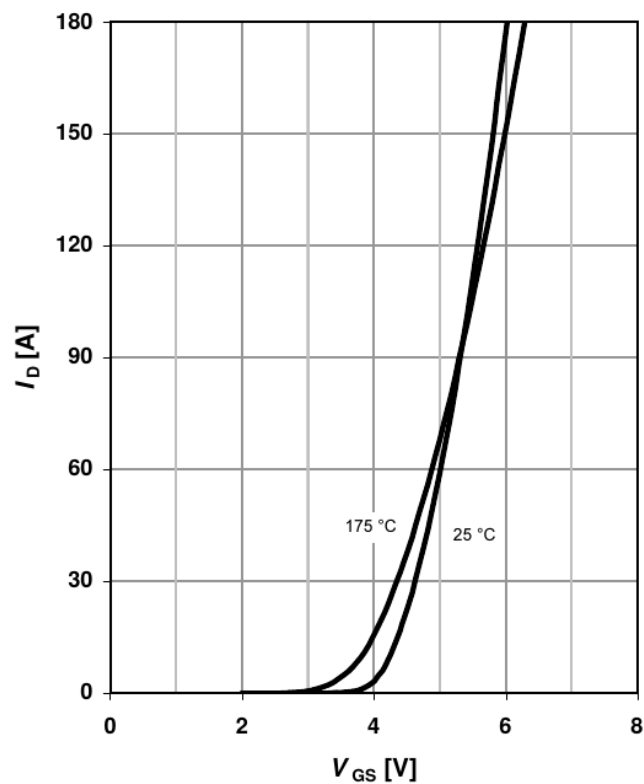


$$I_0 = I_{DS}'' \left(\frac{1}{\omega_n^2} \right) + I_{DS}' \frac{2\xi}{\omega_n} + I_{DS}$$



$$\zeta = \frac{g_m L_s + R_g C_{GS}}{\sqrt{(L_s + L_g) C_{GS}}} = \frac{g_m L_s}{\sqrt{(L_s + L_g) C_{GS}}} + \frac{R_g C_{GS}}{\sqrt{(L_s + L_g) C_{GS}}}$$

- $L_s \sim 7\text{nH}$ (TO-220 ->konec priključka)
- gm:



- $L_s \sim 7\text{nH}$ (TO-220 ->konec priključka)
- gm:

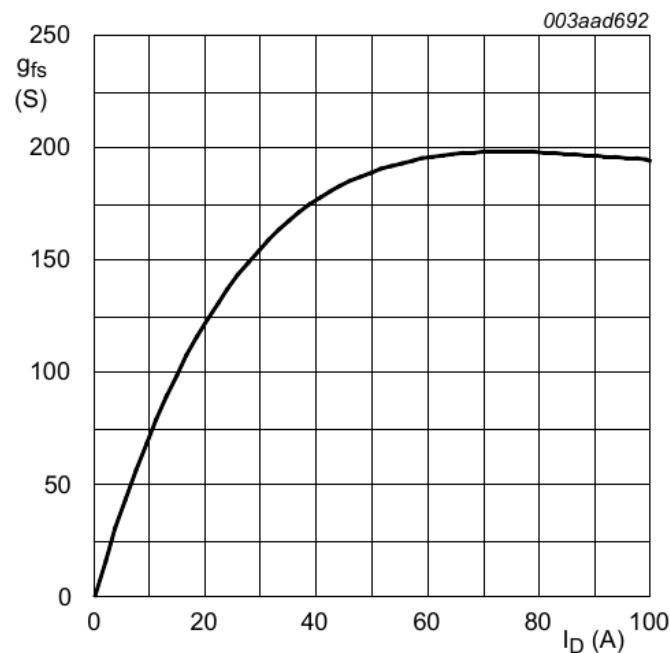
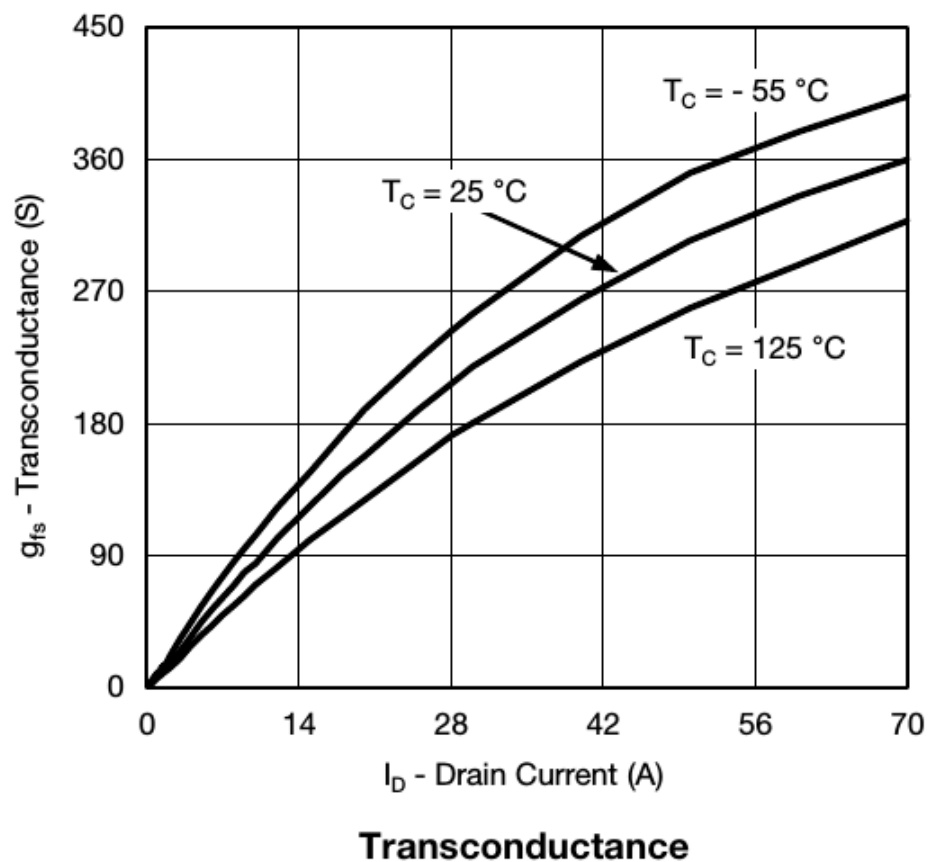


Fig. 6. Forward transconductance as a function of drain current; typical values

- $L_s \sim 7\text{nH}$ (TO-220 ->konec priključka)
- gm:

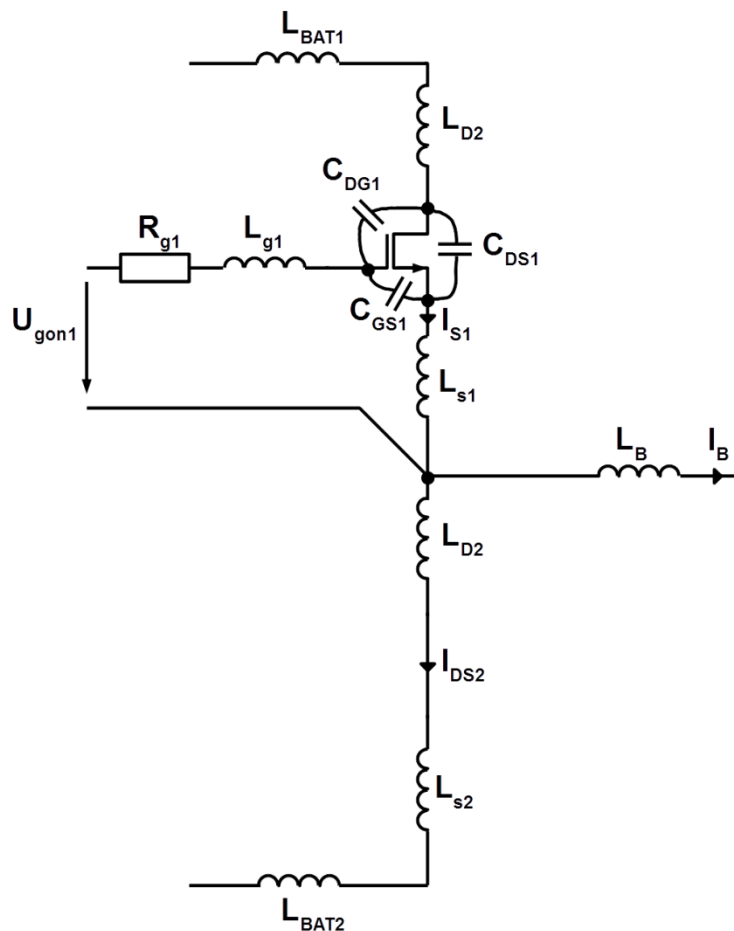


- $L_s * g_m \sim 7\text{nH} * 70\text{A/V} = 490\text{ ns}$
- $R_g * C_{gs} \sim 10\Omega * 10\text{nF} = 100\text{ ns}$

- Če je $g_m \cdot L_s \gg R_g \cdot C_{gs}, R_g \cdot I_g + L_g \cdot I_g' \sim 0$:

$$\frac{d I_{DS}}{dt} \approx \frac{U_{gon} - U_{GS}}{L_s}$$

- Nadomestno vezje, dokler spodnja dioda prevaja in se še preklaplja tok:

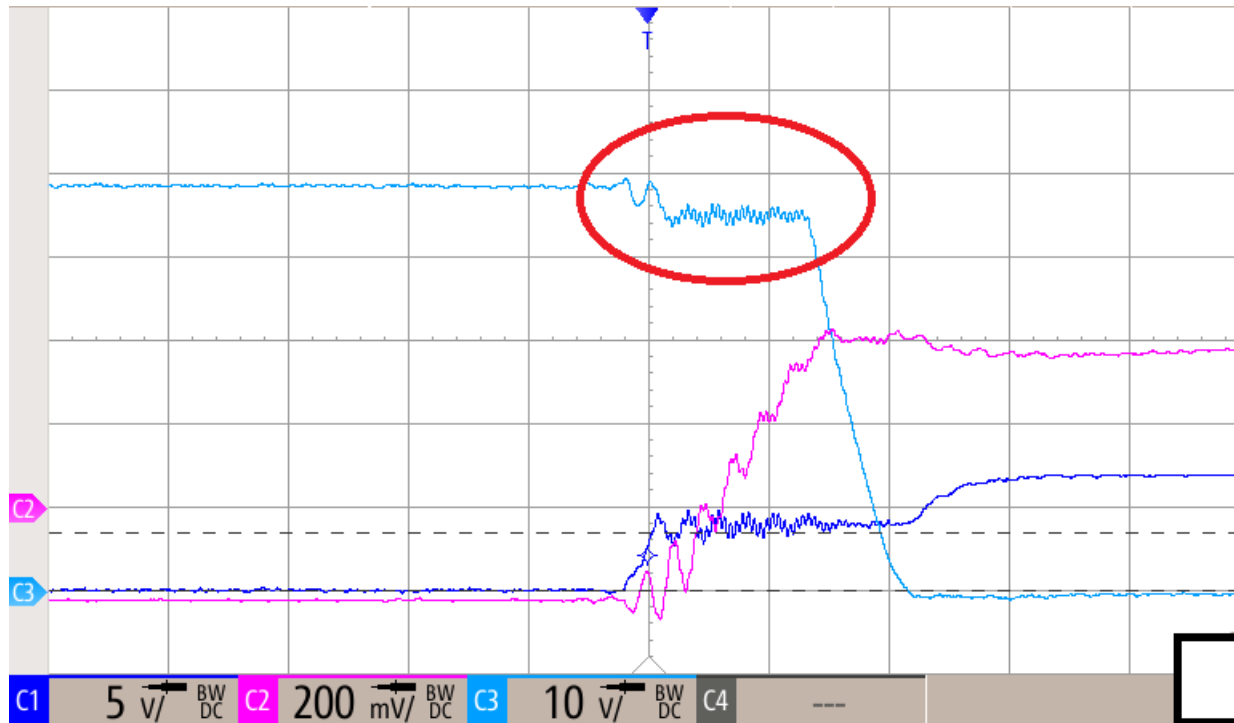


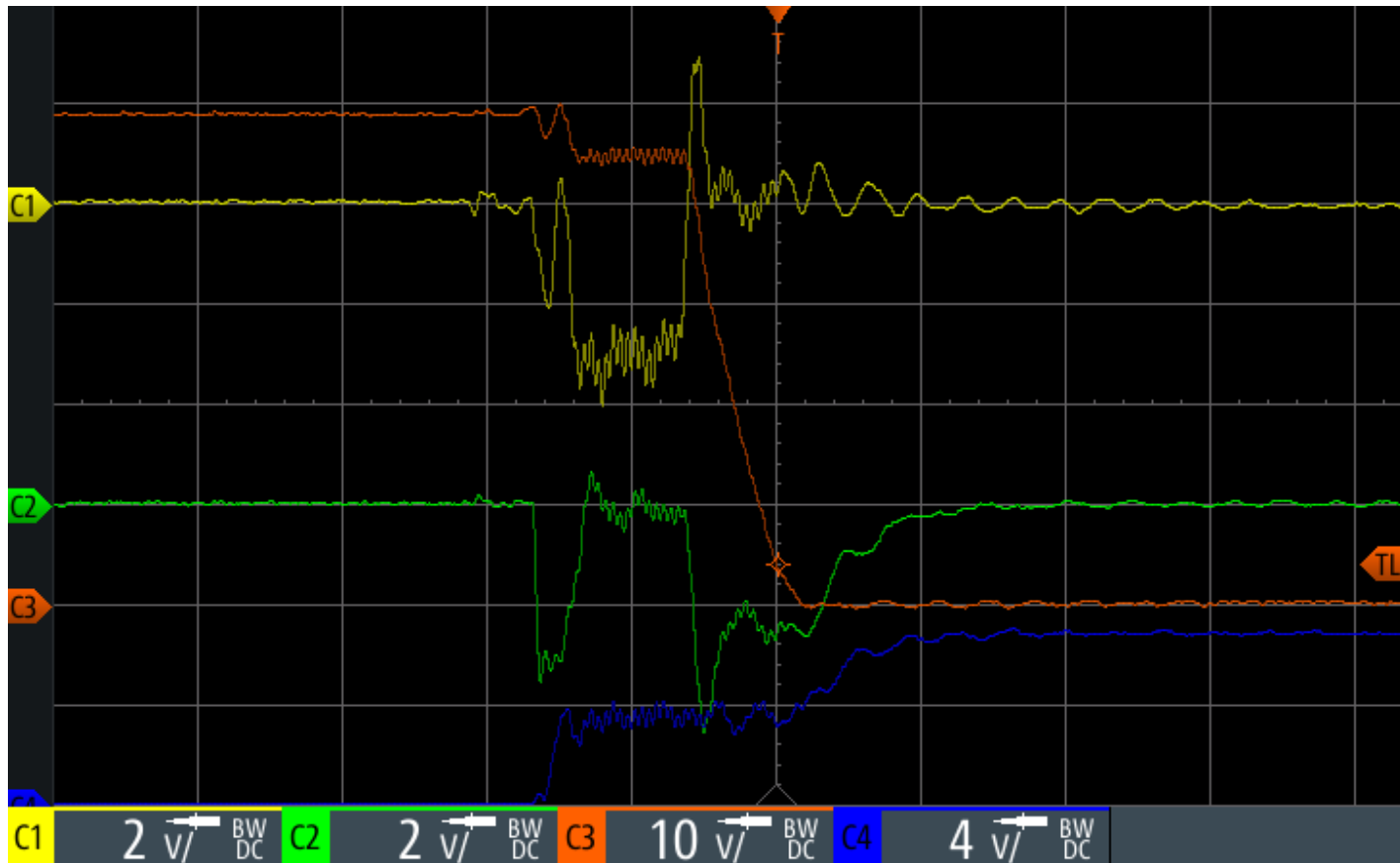
Predpostavke:

- Tok čez R_{g2} , $L_{g2} \ll$ tok čez L_{s2}
- $R_{ds_diff} \sim 0$
- $I_b \sim \text{konst}$
- $I_{ds1} - I_{ds2} = \text{konst}$
- $I_{ds1}' = I_{ds2}'$

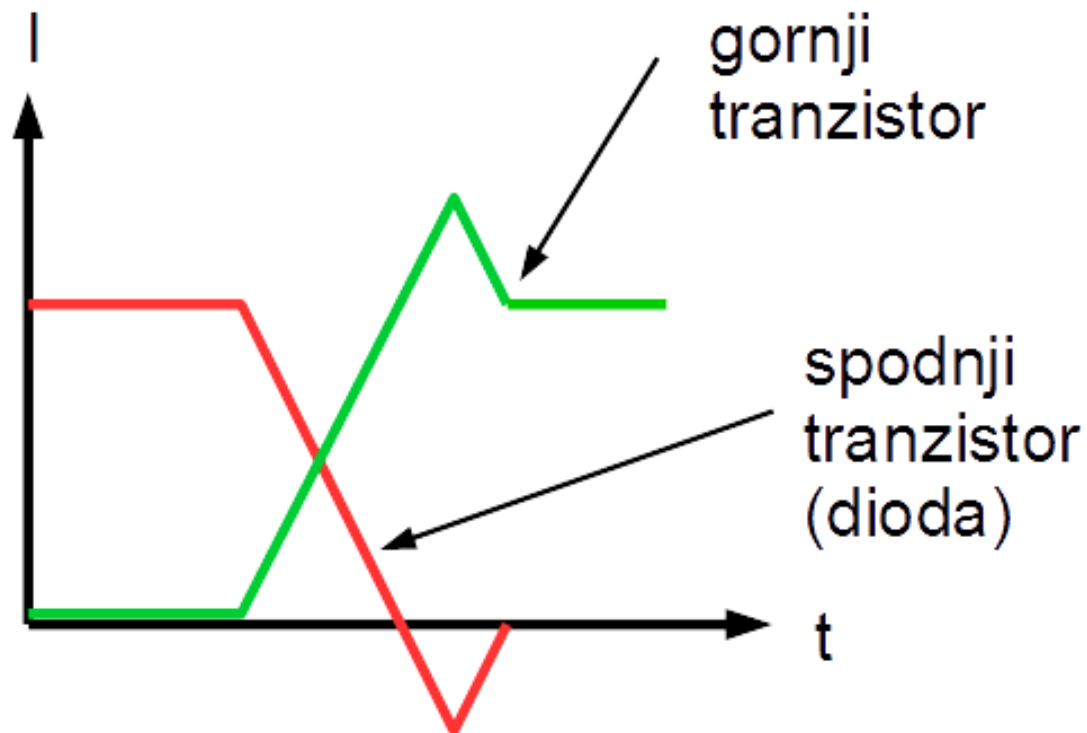
- Med preklopom toka:
- $I_{ds}' \sim \text{konst.}$, torej $U_{ind} = L \cdot I_{ds}' \sim \text{konst.}$
- Padeč napetosti na induktivnostih:

$$\sum U_i = (L_{BAT1} + L_{D1} + L_{S1} + L_{D2} + L_{S2} + L_{BAT2}) \cdot \frac{d I_{DS}}{dt}$$

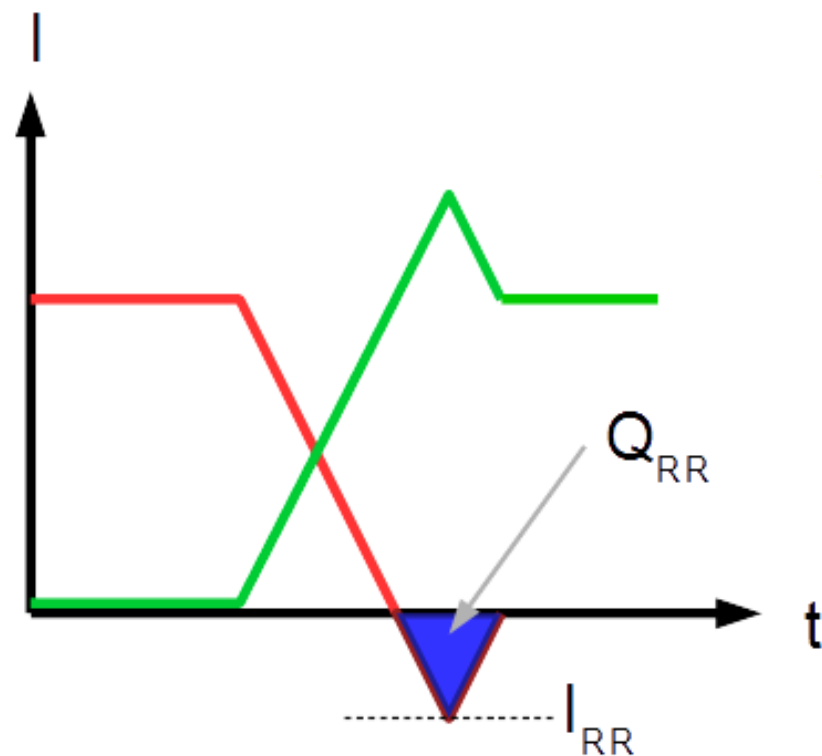




U_{Ls} , U_{Rg} , U_{GS} , U_{DS}



Izgube zaradi rekombinacij:



$$W_{RR} = \int I_{RR} \cdot U_{DS} dt = U_{DS} \cdot \int I_{RR} dt = Q_{RR} \cdot U_{DS}$$

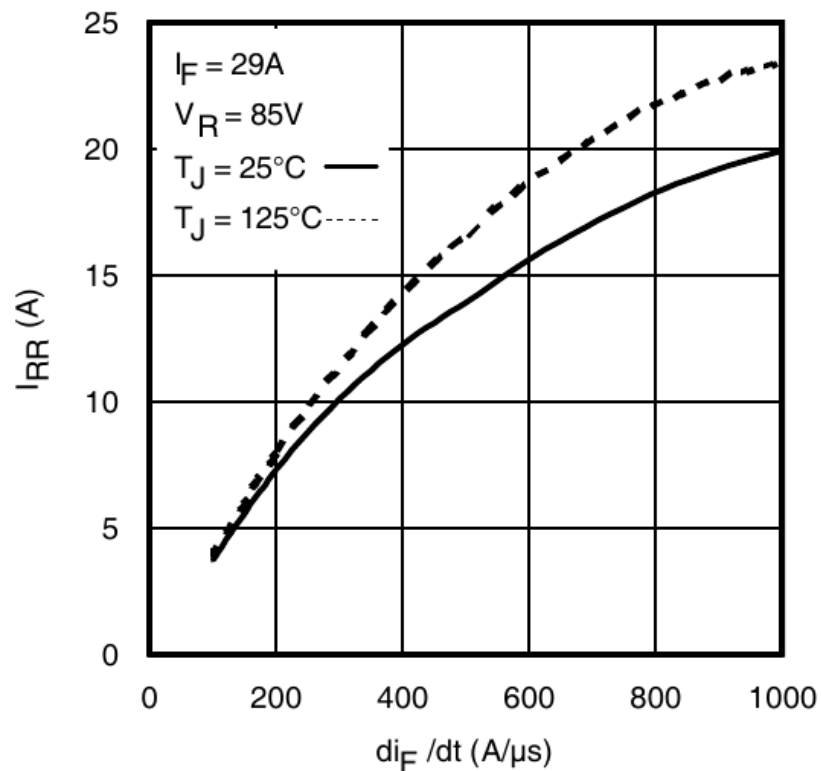


Fig. 17 - Typical Recovery Current vs. di_F/dt

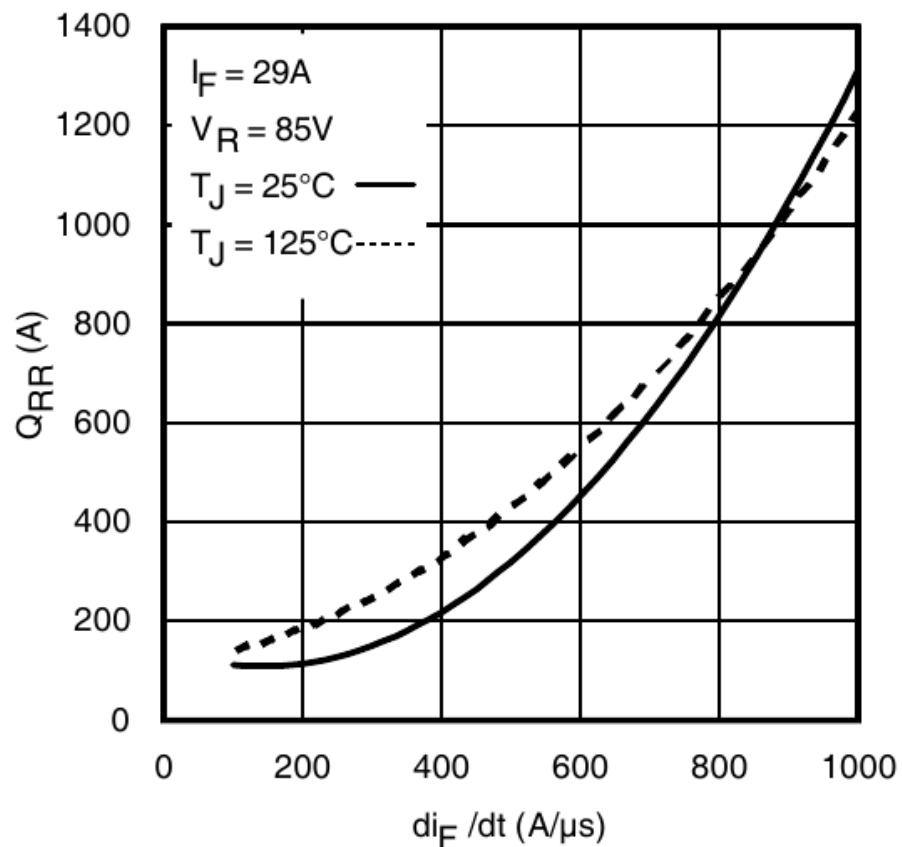
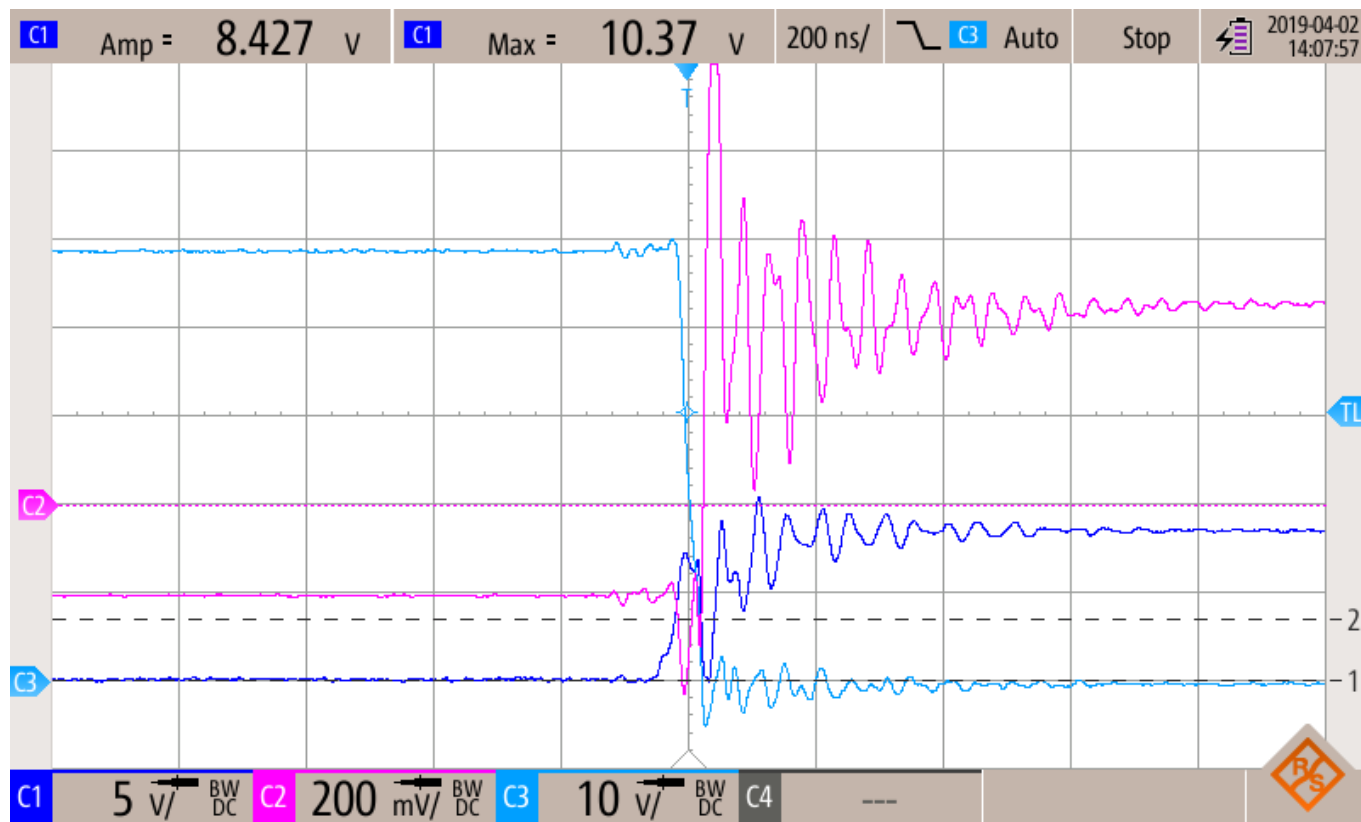
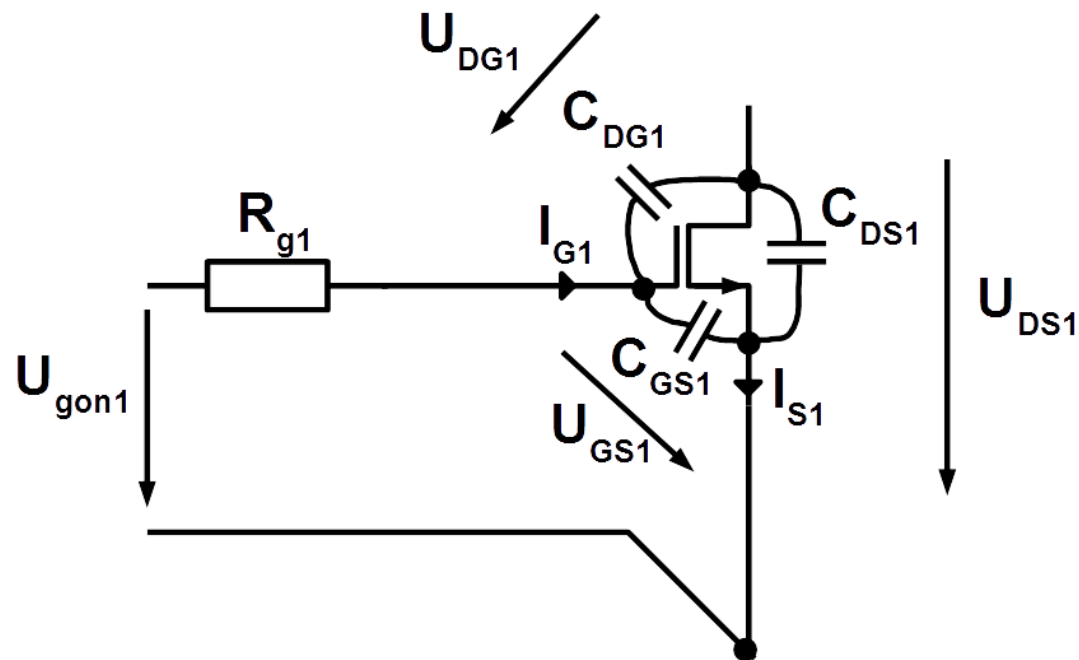


Fig. 19 - Typical Stored Charge vs. di_F/dt

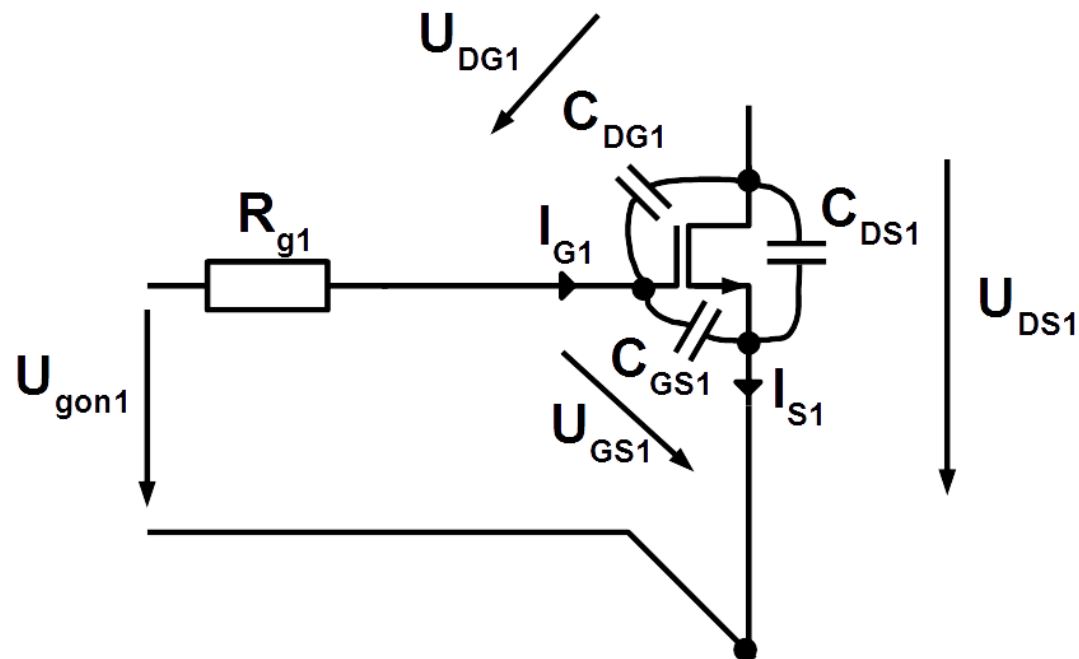


Preklop napetosti

- Med preklopom napetosti (in tudi med preklopom toka) se U_{gs} ne pretirano spreminja (rekurzivni argument?)
- Izprazniti moramo kapacitivnosti C_{dg} in C_{gs} gornjega tranzistorja
- Strmina spreminjanja U_{dg} je približno konstantna

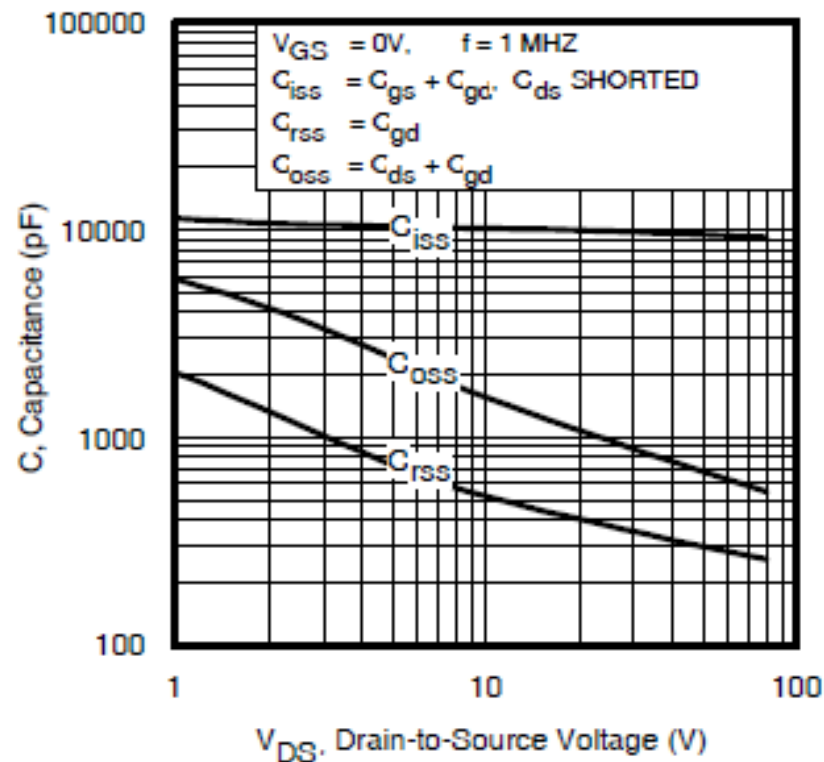
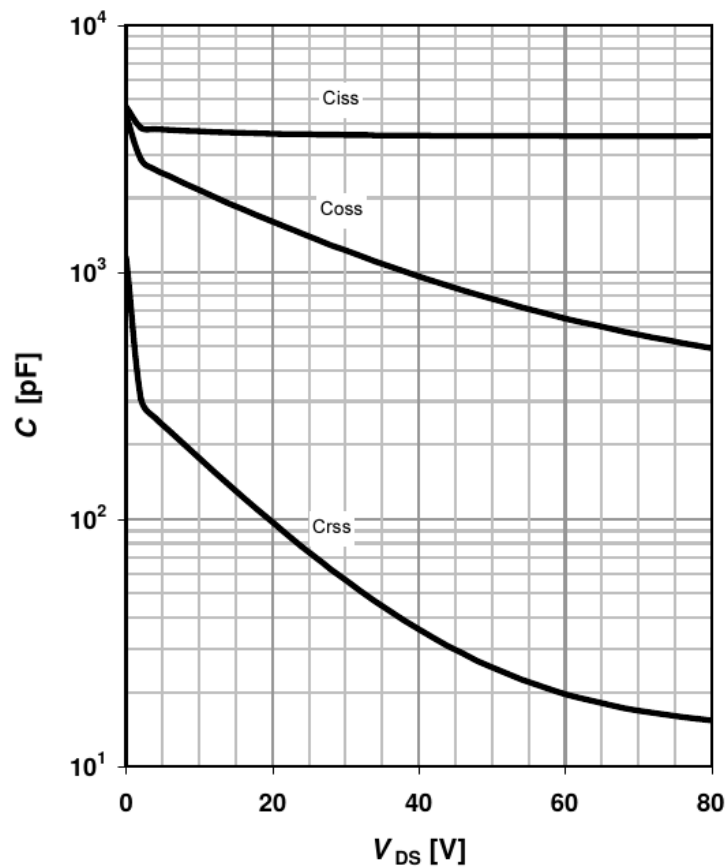


$$I_g \approx \frac{U_{gon} - U_{GS}}{R_g} = -I_{DG}$$



$$\frac{dU_{DG}}{dt} = \frac{I_{DG}}{C_{DG}} \approx -\frac{U_{gon} - U_{GS}}{R_g C_{DG}}$$





Prevajanje

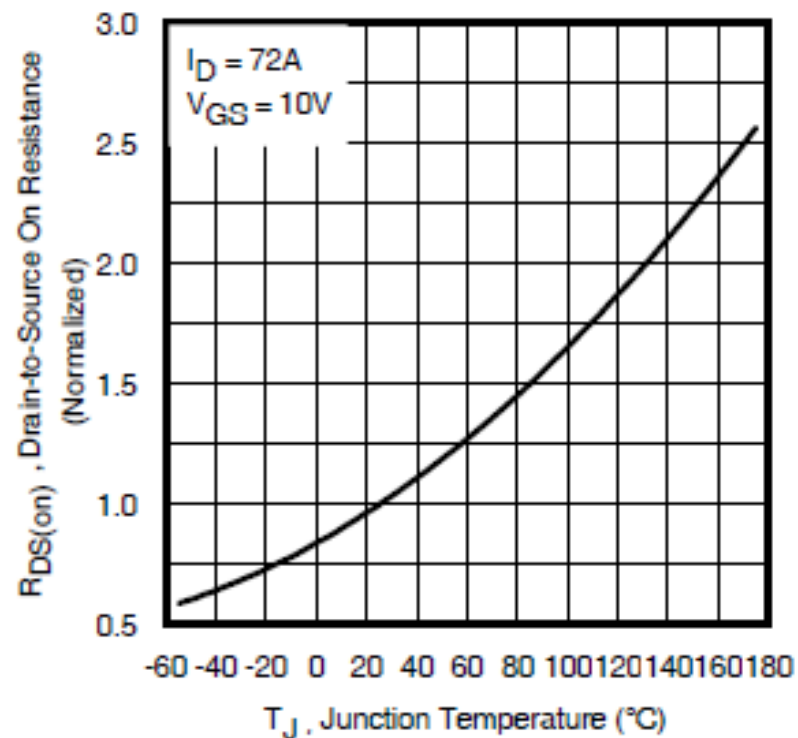
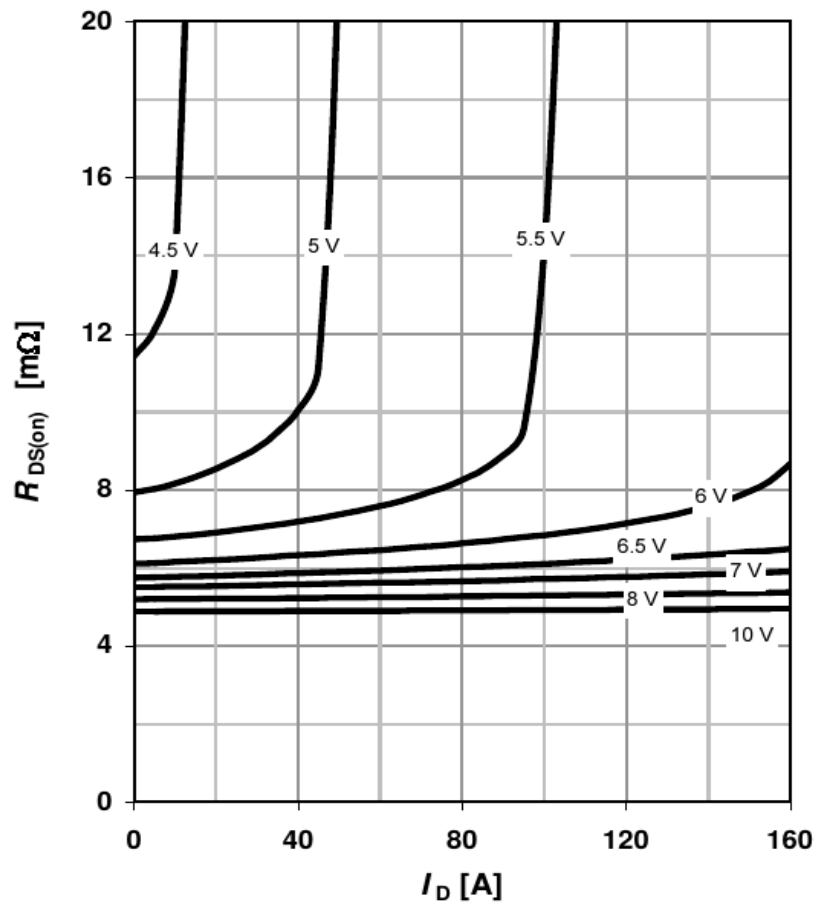
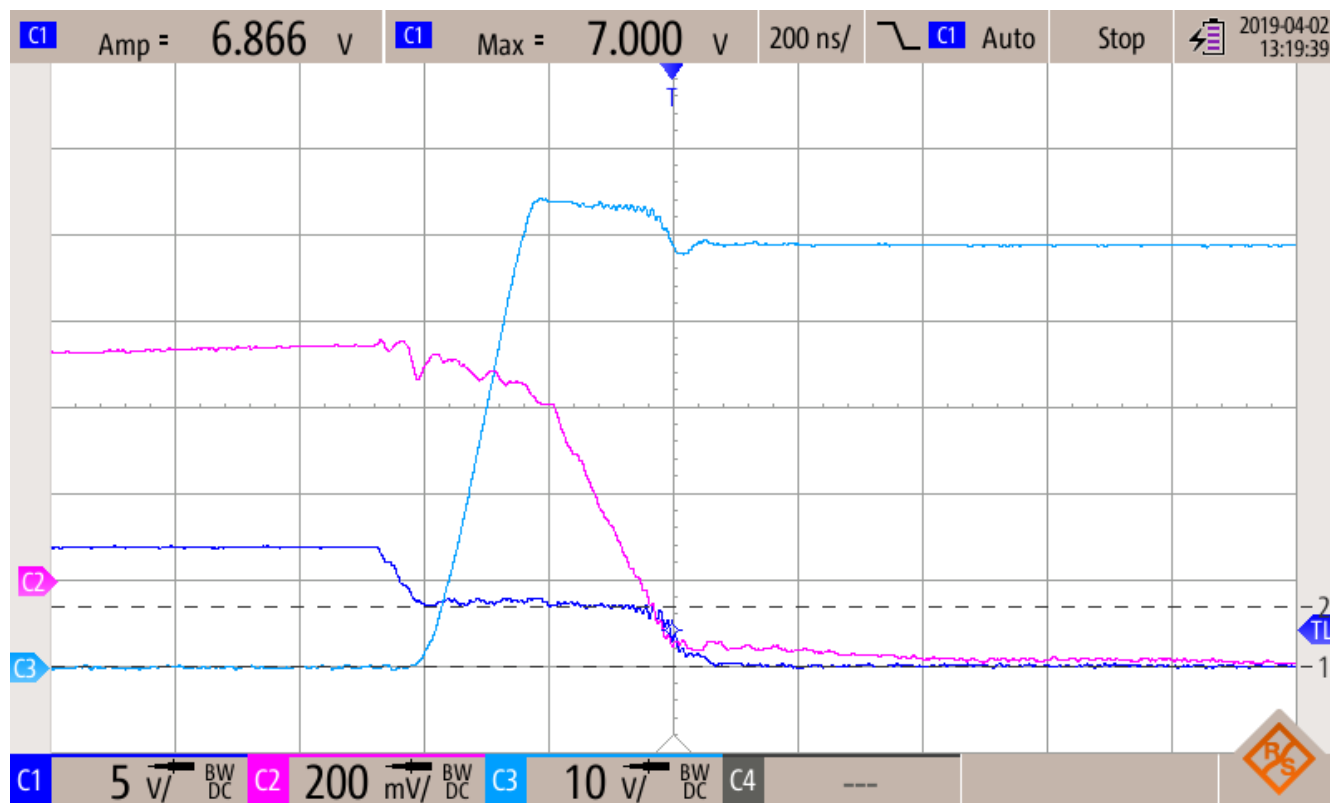
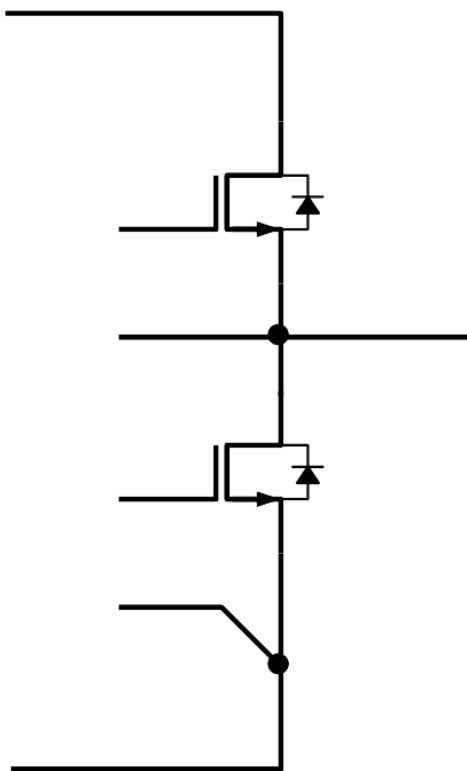


Fig 4. Normalized On-Resistance vs. Temperature

Izklop

■ Najprej se preklopi napetost, nato tok



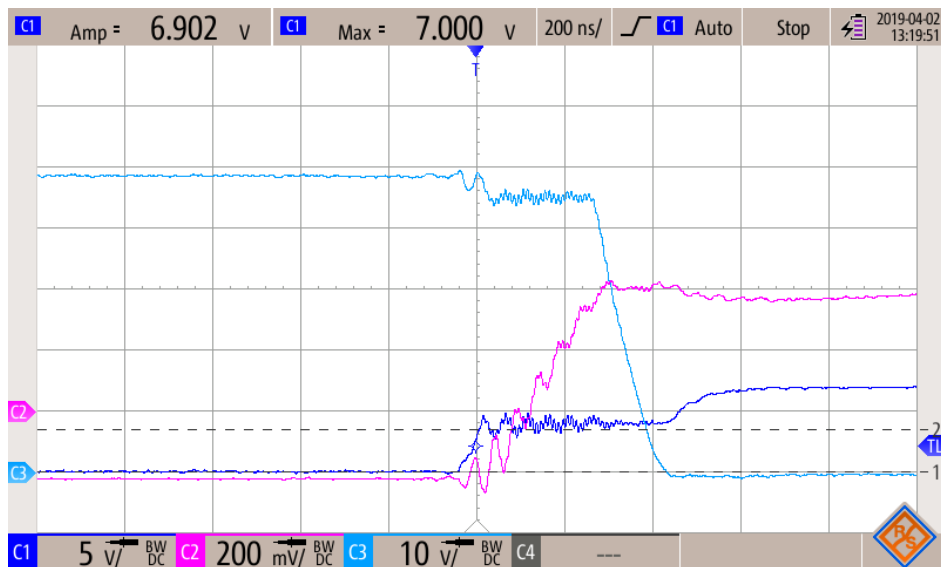


U_{Ls} , U_{Rg} , U_{GS} , U_{DS}

$$\frac{dU_{DG}}{dt} \approx \frac{U_{GS}}{R_g C_{DG}}$$

$$\frac{dI_{DS}}{dt} \approx \frac{-U_{GS}}{L_s} \approx \textit{konst.}$$

(pri pogoju $g_m \cdot L_s \gg R_g \cdot C_{gs}$)



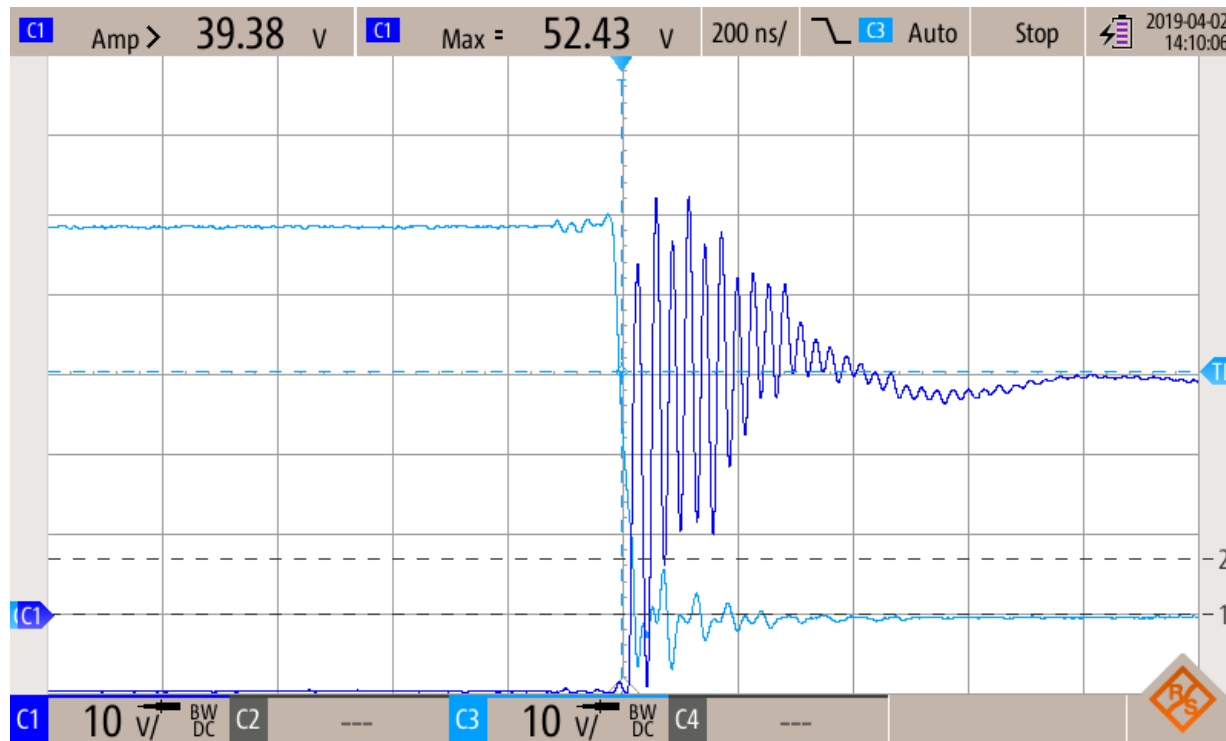
Drugi primeri

Drugi primeri

Minimalna Ls



Driven by performance



U_{DS1} , U_{DS2}

Drugi primeri

Majhna Ls + dodan Cdg



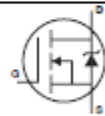
Driven by performance



U_{DS1} , U_{DS2}

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	260	—	—	S	$V_{DS} = 50V, I_D = 43A$
Q_g	Total Gate Charge	—	190	290	nC	$I_D = 43A$ $V_{DS} = 50V$ $V_{GS} = 10V$ ④
Q_{gs}	Gate-to-Source Charge	—	40	—		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	49	—		
R_G	Gate Resistance	—	1.3	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	24	—	ns	$V_{DD} = 65V$ $I_D = 43A$ $R_G = 2.6\Omega$ $V_{GS} = 10V$ ④
t_r	Rise Time	—	58	—		
$t_{d(off)}$	Turn-Off Delay Time	—	81	—		
t_f	Fall Time	—	71	—		
C_{iss}	Input Capacitance	—	9540	—	pF	$V_{GS} = 0V$ $V_{DS} = 50V$ $f = 1.0MHz$ $V_{GS} = 0V, V_{DS} = 0V$ to 80V ⑥ $V_{GS} = 0V, V_{DS} = 0V$ to 80V ⑤
C_{oss}	Output Capacitance	—	680	—		
C_{riss}	Reverse Transfer Capacitance	—	300	—		
$C_{oss\ eff. (ER)}$	Effective Output Capacitance (Energy Related) ④	—	760	—		
$C_{oss\ eff. (TR)}$	Effective Output Capacitance (Time Related) ⑤	—	1120	—		

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	72	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ②③	—	—	290		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ C, I_S = 43A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	50	75	ns	$T_J = 25^\circ C$ $V_R = 85V,$ $T_J = 125^\circ C$ $I_F = 43A$ $di/dt = 10UA/\mu s$ ④
Q_{rr}	Reverse Recovery Charge	—	100	150	nC	
		—	140	210		
I_{RRM}	Reverse Recovery Current	—	3.5	—	A	$T_J = 25^\circ C$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				



Unotisto!